

ABSTRACT**Semiconductor Device Comprising a
Field-Effect Transistor in a
Silicon-On-Insulator Structure**

The present invention relates to a semiconductor device, comprising a semiconductor-on-insulator, SeOI, structure comprising a substrate, an oxide layer on the substrate and a semiconductor layer on the oxide layer; with a field-effect-transistor, FET, wherein the FET comprises a channel region in the substrate; a dielectric being at least a part of the oxide layer of the SeOI structure; and a gate at least partially being a first part of the semiconductor of the SeOI structure.

Figure 2a.